

### General Description

The WSR80N06 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

### Features

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation

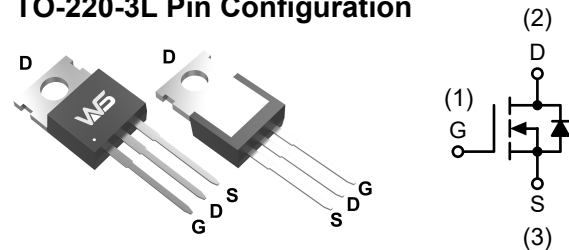
### Product Summary

BV <sub>DSS</sub>	R <sub>DSON</sub>	I <sub>D</sub>
60V	9.1mΩ	80A

### Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

### TO-220-3L Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	60	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	80	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	50	A
	Pulsed Drain Current <sup>2</sup>	300	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	450	mJ
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	110	W
T <sub>J</sub> T <sub>STG</sub>	Operating Junction Temperature Range	-55 to 175	°C

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	0.57	°C/W

### Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.057	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	---	9.1	11.5	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	2.0	3.0	4.0	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.68	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =15A	20	---	---	S
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =30V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =30A	---	36	45	nC
Q <sub>gs</sub>	Gate-Source Charge		---	9.9	18	
Q <sub>gd</sub>	Gate-Drain Charge		---	6.6	15	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =2A, R=1Ω.	---	10	21	ns
T <sub>r</sub>	Rise Time		---	16	28	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	12	22	
T <sub>f</sub>	Fall Time		---	45	65	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz	---	2350	2925	pF
C <sub>oss</sub>	Output Capacitance		---	237	298	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	205	251	

### Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	80	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	IF=80A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	28	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	49	---	nC

### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E<sub>AS</sub> condition : T<sub>J</sub>=25°C, V<sub>DD</sub>=30V, V<sub>G</sub>=10V, L=0.5mH, R<sub>g</sub>=25Ω



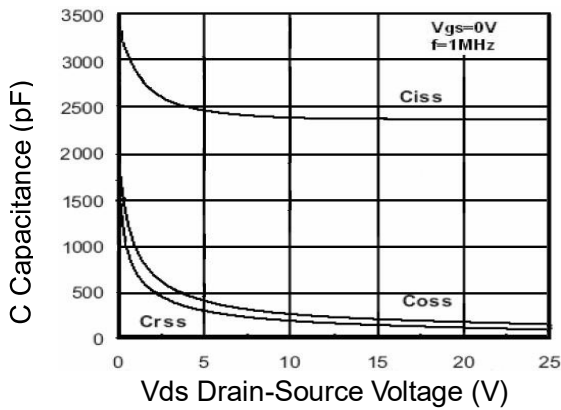


Figure 7 Capacitance vs Vds

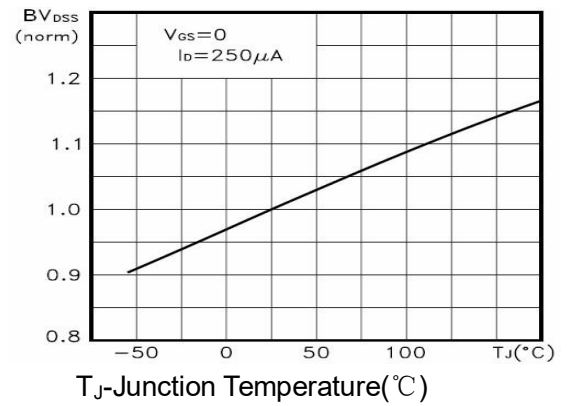


Figure 9  $BV_{DSS}$  vs Junction Temperature

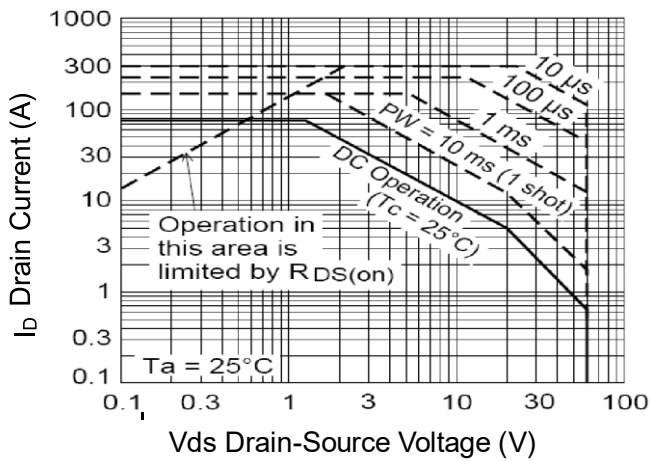


Figure 8 Safe Operation Area

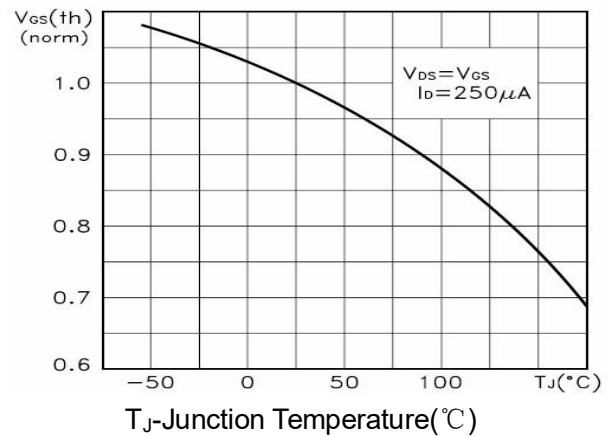


Figure 10  $V_{GS(th)}$  vs Junction Temperature

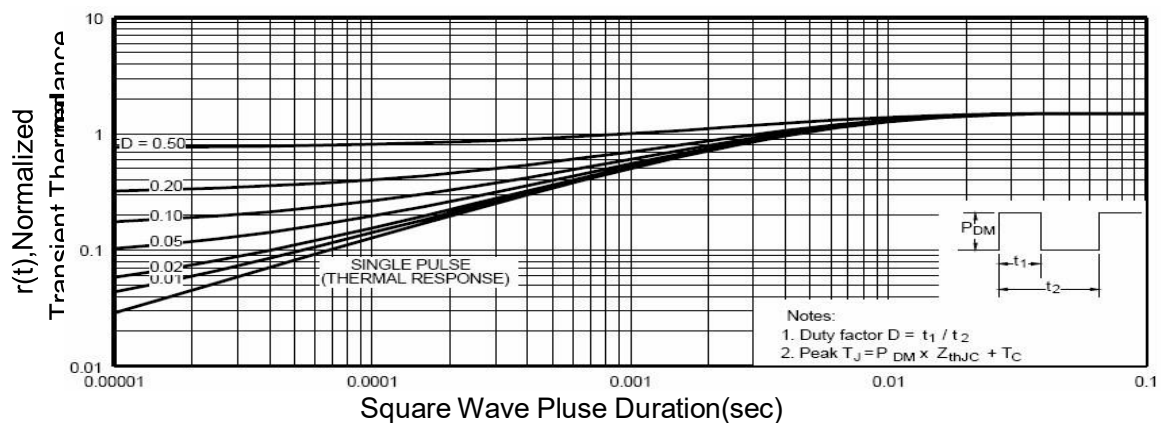


Figure 11 Normalized Maximum Transient Thermal Impedance

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